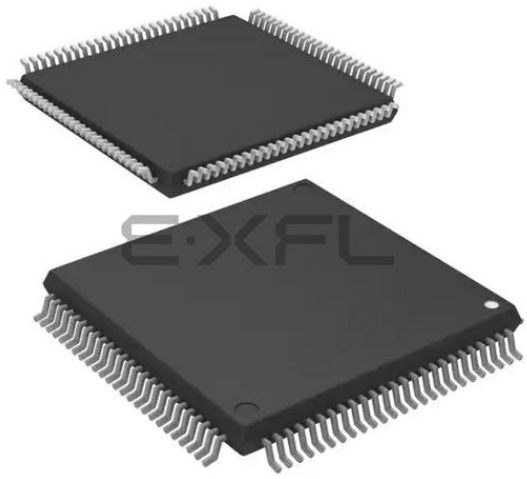
Renesas Electronics America Inc - M30622F8PGP#U5C Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	M16C/60
Core Size	16-Bit
Speed	24MHz
Connectivity	I²C, IEBus, UART/USART
Peripherals	DMA, WDT
Number of I/O	85
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LFQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/m30622f8pgp-u5c

1. Overview

The M16C/62P Group (M16C/62P, M16C/62PT) of single-chip microcomputers are built using the high performance silicon gate CMOS process using a M16C/60 Series CPU core and are packaged in a 80-pin, 100-pin and 128-pin plastic molded QFP. These single-chip microcomputers operate using sophisticated instructions featuring a high level of instruction efficiency. With 1M bytes of address space, they are capable of executing instructions at high speed. In addition, this microcomputer contains a multiplier and DMAC which combined with fast instruction processing capability, makes it suitable for control of various OA, communication, and industrial equipment which requires high-speed arithmetic/logic operations.

1.1 Applications

Audio, cameras, television, home appliance, office/communications/portable/industrial equipment, automobile, etc.

Specifications written in this manual are believed to be accurate, but are not guaranteed to be entirely free of error. Specifications in this manual may be changed for functional or performance improvements. Please make sure your manual is the latest edition.

1.2 Performance Outline

Table 1.1 to 1.3 list Performance Outline of M16C/62P Group (M16C/62P, M16C/62PT)(128-pin version).

Table 1.1 Performance Outline of M16C/62P Group (M16C/62P, M16C/62PT)(128-pin version)

	Item	Performance
		M16C/62P
CPU	Number of Basic Instructions	91 instructions
	Minimum Instruction Execution Time	41.7ns(f(BCLK)=24MHz, VCC1=3.3 to 5.5V) 100ns(f(BCLK)=10MHz, VCC1=2.7 to 5.5V)
	Operating Mode	Single-chip, memory expansion and microprocessor mode
	Address Space	1 Mbyte (Available to 4 Mbytes by memory space expansion function)
	Memory Capacity	See **Table 1.4 to 1.5 Product List**
Peripheral Function	Port	Input/Output : 113 pins, Input : 1 pin
	Multifunction Timer	Timer A : 16 bits x 5 channels, Timer B : 16 bits x 6 channels, Three phase motor control circuit
	Serial Interface	3 channels Clock synchronous, UART, I2C bus(1), IEBus(2) 2 channels Clock synchronous
	A/D Converter	10-bit A/D converter: 1 circuit, 26 channels
	D/A Converter	8 bits x 2 channels
	DMAC	2 channels
	CRC Calculation Circuit	CCITT-CRC
	Watchdog Timer	15 bits x 1 channel (with prescaler)
	Interrupt	Internal: 29 sources, External: 8 sources, Software: 4 sources, Priority level: 7 levels
	Clock Generation Circuit	4 circuits Main clock generation circuit (*), Subclock generation circuit (*), On-chip oscillator, PLL synthesizer (*)Equipped with a built-in feedback resistor.
	Oscillation Stop Detection Function	Stop detection of main clock oscillation, re-oscillation detection function
	Voltage Detection Circuit	Available (option(4))
Electric Characteristics	Supply Voltage	VCC1=3.0 to 5.5 V, VCC2=2.7V to VCC1 (f(BCLK=24MHz) VCC1=2.7 to 5.5 V, VCC2=2.7V to VCC1 (f(BCLK=10MHz)
	Power Consumption	14 mA (VCC1=VCC2=5V, f(BCLK)=24MHz) 8 mA (VCC1=VCC2=3V, f(BCLK)=10MHz) 1.8μA (VCC1=VCC2=3V, f(XCIN)=32kHz, wait mode) 0.7μA (VCC1=VCC2=3V, stop mode)
Flash memory version	Program/Erase Supply Voltage	3.3±0.3 V or 5.0±0.5 V
	Program and Erase Endurance	100 times (all area) or 1,000 times (user ROM area without block A and block 1) / 10,000 times (block A, block 1) (3)
Operating Ambient Temperature		-20 to 85°C, -40 to 85°C (3)
Package		128-pin plastic mold LQFP

NOTES:
1. I2C bus is a registered trademark of Koninklijke Philips Electronics N. V.
2. IEBus is a registered trademark of NEC Electronics Corporation.
3. See **Table 1.8 Product Code** for the program and erase endurance, and operating ambient temperature. In addition 1,000 times/10,000 times are under development as of Jul., 2005. Please inquire about a release schedule.
4. All options are on request basis.

Table 1.6 Product List (3) (T version (M16C/62PT)) As of Dec. 2005

Type No.	ROM Capacity	RAM Capacity	Package Type (1)	Remarks	
M3062CM6T-XXXFP (D)	48 Kbytes	4 Kbytes	PRQP0100JB-A	Mask ROM version	T Version (High reliability 85°C version)
M3062CM6T-XXXGP (D)			PLQP0100KB-A		
M3062EM6T-XXXGP (P)			PRQP0080JA-A		
M3062CM8T-XXXFP (D)	64 Kbytes	4 Kbytes	PRQP0100JB-A		
M3062CM8T-XXXGP (D)			PLQP0100KB-A		
M3062EM8T-XXXGP (P)			PRQP0080JA-A		
M3062CMAT-XXXFP (D)	96 Kbytes	5 Kbytes	PRQP0100JB-A		
M3062CMAT-XXXGP (D)			PLQP0100KB-A		
M3062EMAT-XXXGP (P)			PRQP0080JA-A		
M3062AMCT-XXXFP (D)	128 Kbytes	10 Kbytes	PRQP0100JB-A		
M3062AMCT-XXXGP (D)			PLQP0100KB-A		
M3062BMCT-XXXGP (P)			PRQP0080JA-A		
M3062CF8TFP (D)	64 K+4 Kbytes	4 Kbytes	PRQP0100JB-A	Flash memory version (2)	
M3062CF8TGP			PLQP0100KB-A		
M3062AFCTFP (D)	128K+4 Kbytes	10 Kbytes	PRQP0100JB-A		
M3062AFCTGP (D)			PLQP0100KB-A		
M3062BFCTGP (P)			PRQP0080JA-A		
M3062JFHTFP (D)	384K+4 Kbytes	31 Kbytes	PRQP0100JB-A		
M3062JFHTGP (D)			PLQP0100KB-A		

(D): Under development
(P): Under planning
NOTES:

1. The old package type numbers of each package type are as follows.
   PRQP0100JB-A : 100P6S-A,
   PLQP0100KB-A : 100P6Q-A,
   PRQP0080JA-A : 80P6S-A
2. In the flash memory version, there is 4K bytes area (block A).

Table 1.12 Pin Characteristics for 128-Pin Package (3)

Pin No.	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
101		P1_2					D10
102		P1_1					D9
103		P1_0					D8
104		P0_7				AN0_7	D7
105		P0_6				AN0_6	D6
106		P0_5				AN0_5	D5
107		P0_4				AN0_4	D4
108		P0_3				AN0_3	D3
109		P0_2				AN0_2	D2
110		P0_1				AN0_1	D1
111		P0_0				AN0_0	D0
112		P11_7					
113		P11_6					
114		P11_5					
115		P11_4					
116		P11_3					
117		P11_2					
118		P11_1					
119		P11_0					
120		P10_7	$\overline{KI3}$			AN7	
121		P10_6	$\overline{KI2}$			AN6	
122		P10_5	$\overline{KI1}$			AN5	
123		P10_4	$\overline{KI0}$			AN4	
124		P10_3				AN3	
125		P10_2				AN2	
126		P10_1				AN1	
127	AVSS						
128		P10_0				AN0	

Table 1.15 Pin Characteristics for 80-Pin Package (1)

Pin No.	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
1		P9_5			CLK4	ANEX0	
2		P9_4		TB4IN		DA1	
3		P9_3		TB3IN		DA0	
4		P9_2		TB2IN	SOUT3		
5		P9_0		TB0IN	CLK3		
6	CNVSS (BYTE)						
7	XCIN	P8_7					
8	XCOUT	P8_6					
9	$\overline{\text{RESET}}$						
10	XOUT						
11	VSS						
12	XIN						
13	VCC1						
14		P8_5	$\overline{\text{NMI}}$				
15		P8_4	$\overline{\text{INT2}}$	ZP			
16		P8_3	$\overline{\text{INT1}}$				
17		P8_2	$\overline{\text{INT0}}$				
18		P8_1		TA4IN			
19		P8_0		TA4OUT			
20		P7_7		TA3IN			
21		P7_6		TA3OUT			
22		P7_1		TA0IN/TB5IN	RXD2/SCL2		
23		P7_0		TA0OUT	TXD2/SDA2		
24		P6_7			TXD1/SDA1		
25		P6_6			RXD1/SCL1		
26		P6_5			CLK1		
27		P6_4			$\overline{\text{CTS1}}$/$\overline{\text{RTS1}}$/$\overline{\text{CTS0}}$/CLKS1		
28		P6_3			TXD0/SDA0		
29		P6_2			RXD0/SCL0		
30		P6_1			CLK0		
31		P6_0			$\overline{\text{CTS0}}$/$\overline{\text{RTS0}}$		
32		P5_7					CLKOUT
33		P5_6					
34		P5_5					
35		P5_4					
36		P5_3					
37		P5_2					
38		P5_1					
39		P5_0					
40		P4_3					
41		P4_2					
42		P4_1					
43		P4_0					
44		P3_7					
45		P3_6					
46		P3_5					
47		P3_4					
48		P3_3					
49		P3_2					
50		P3_1					

Table 1.20 Pin Description (80-pin Version) (1) (1)

Signal Name	Pin Name	I/O Type	Power Supply	Description
Power supply input	VCC1, VSS	I	–	Apply 2.7 to 5.5 V to the VCC1 pin and 0 V to the VSS pin. (1, 2)
Analog power supply input	AVCC AVSS	I	VCC1	Applies the power supply for the A/D converter. Connect the AVCC pin to VCC1. Connect the AVSS pin to VSS.
Reset input	$\overline{\text{RESET}}$	I	VCC1	The microcomputer is in a reset state when applying "L" to the this pin.
CNVSS	CNVSS (BYTE)	I	VCC1	Switches processor mode. Connect this pin to VSS to when after a reset to start up in single-chip mode. Connect this pin to VCC1 to start up in microprocessor mode. As for the BYTE pin of the 80-pin versions, pull-up processing is performed within the microcomputer.
Main clock input	XIN	I	VCC1	I/O pins for the main clock generation circuit. Connect a ceramic resonator or crystal oscillator between XIN and XOUT (3). To use the external clock, input the clock from XIN and leave XOUT open.
Main clock output	XOUT	O	VCC1	
Sub clock input	XCIN	I	VCC1	I/O pins for a sub clock oscillation circuit. Connect a crystal oscillator between XCIN and XCOUT (3). To use the external clock, input the clock from XCIN and leave XCOUT open.
Sub clock output	XCOUT	O	VCC1	
Clock output	CLKOUT	O	VCC2	The clock of the same cycle as fC, f8, or f32 is outputted.
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}$ to $\overline{\text{INT2}}$	I	VCC1	Input pins for the $\overline{\text{INT}}$ interrupt.
$\overline{\text{NMI}}$ interrupt input	$\overline{\text{NMI}}$	I	VCC1	Input pin for the $\overline{\text{NMI}}$ interrupt.
Key input interrupt input	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	VCC1	Input pins for the key input interrupt.
Timer A	TA0OUT, TA3OUT, TA4OUT	I/O	VCC1	These are Timer A0,Timer A3 and Timer A4 I/O pins. (however, output of TA0OUT for the N-channel open drain output.)
	TA0IN, TA3IN, TA4IN	I	VCC1	These are Timer A0, Timer A3 and Timer A4 input pins.
	ZP	I	VCC1	Input pin for the Z-phase.
Timer B	TB0IN, TB2IN to TB5IN	I	VCC1	These are Timer B0, Timer B2 to Timer B5 input pins.
Serial interface	$\overline{\text{CTS0}}$ to $\overline{\text{CTS1}}$	I	VCC1	These are send control input pins.
	$\overline{\text{RTS0}}$ to $\overline{\text{RTS1}}$	O	VCC1	These are receive control output pins.
	CLK0, CLK1, CLK3, CLK4	I/O	VCC1	These are transfer clock I/O pins.
	RXD0 to RXD2	I	VCC1	These are serial data input pins.
	SIN4	I	VCC1	This is serial data input pin.
	TXD0 to TXD2	O	VCC1	These are serial data output pins. (however, output of TXD2 for the N-channel open drain output.)
	SOUT3, SOUT4	O	VCC1	These are serial data output pins.
	CLKS1	O	VCC1	This is output pin for transfer clock output from multiple pins function.
I^2C mode	SDA0 to SDA2	I/O	VCC1	These are serial data I/O pins. (however, output of SDA2 for the N-channel open drain output.)
	SCL0 to SCL2	I/O	VCC1	These are transfer clock I/O pins. (however, output of SCL2 for the N-channel open drain output.)

I : Input O : Output I/O : Input and output

NOTES:
1. In this manual, hereafter, VCC refers to VCC1 unless otherwise noted.
2. In M16C/62PT, apply 4.0 to 5.5 V to the VCC1 pin.
3. Ask the oscillator maker the oscillation characteristic.

2.8.8 Stack Pointer Select Flag (U Flag)

ISP is selected when the U flag is “0”; USP is selected when the U flag is “1”.
The U flag is cleared to “0” when a hardware interrupt request is accepted or an INT instruction for software interrupt Nos. 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is configured with three bits, for specification of up to eight processor interrupt priority levels from level 0 to level 7.
If a requested interrupt has priority greater than IPL, the interrupt is enabled.

2.8.10 Reserved Area

When write to this bit, write “0”. When read, its content is indeterminate.

4. Special Function Register (SFR)

SFR(Special Function Register) is the control register of peripheral functions. Tables 4.1 to 4.6 list the SFR information.

Table 4.1 SFR Information (1) (1)

Address	Register	Symbol	After Reset
0000h			
0001h			
0002h			
0003h			
0004h	Processor Mode Register 0 (2)	PM0	00000000b(CNVSS pin is "L") 00000011b(CNVSS pin is "H")
0005h	Processor Mode Register 1	PM1	00001000b
0006h	System Clock Control Register 0	CM0	01001000b
0007h	System Clock Control Register 1	CM1	00100000b
0008h	Chip Select Control Register (6)	CSR	00000001b
0009h	Address Match Interrupt Enable Register	AIER	XXXXXX00b
000Ah	Protect Register	PRCR	XX000000b
000Bh	Data Bank Register (6)	DBR	00h
000Ch	Oscillation Stop Detection Register (3)	CM2	0X000000b
000Dh			
000Eh	Watchdog Timer Start Register	WDTS	XXh
000Fh	Watchdog Timer Control Register	WDC	00XXXXXXb (4)
0010h 0011h 0012h	Address Match Interrupt Register 0	RMAD0	00h 00h X0h
0013h			
0014h 0015h 0016h	Address Match Interrupt Register 1	RMAD1	00h 00h X0h
0017h			
0018h			
0019h	Voltage Detection Register 1 (5, 6)	VCR1	00001000b
001Ah	Voltage Detection Register 2 (5, 6)	VCR2	00h
001Bh	Chip Select Expansion Control Register (6)	CSE	00h
001Ch	PLL Control Register 0	PLC0	0001X010b
001Dh			
001Eh	Processor Mode Register 2	PM2	XXX00000b
001Fh	Low Voltage Detection Interrupt Register (6)	D4INT	00h
0020h 0021h 0022h	DMA0 Source Pointer	SAR0	XXh XXh XXh
0023h			
0024h 0025h 0026h	DMA0 Destination Pointer	DAR0	XXh XXh XXh
0027h			
0028h 0029h	DMA0 Transfer Counter	TCR0	XXh XXh
002Ah			
002Bh			
002Ch	DMA0 Control Register	DM0CON	00000X00b
002Dh			
002Eh			
002Fh			
0030h 0031h 0032h	DMA1 Source Pointer	SAR1	XXh XXh XXh
0033h			
0034h 0035h 0036h	DMA1 Destination Pointer	DAR1	XXh XXh XXh
0037h			
0038h 0039h	DMA1 Transfer Counter	TCR1	XXh XXh
003Ah			
003Bh			
003Ch	DMA1 Control Register	DM1CON	00000X00b
003Dh			
003Eh			
003Fh			

NOTES:
1. The blank areas are reserved and cannot be accessed by users.
2. The PM00 and PM01 bits do not change at software reset, watchdog timer reset and oscillation stop detection reset.
3. The CM20, CM21, and CM27 bits do not change at oscillation stop detection reset.
4. The WDC5 bit is "0" (cold start) immediately after power-on. I t can only be set to "1" in a program.
5. This register does not change at software reset, watchdog timer reset and oscillation stop detection reset.
6. This register in M16C/62PT cannot be used.

X : Nothing is mapped to this bit

Table 5.6 Flash Memory Version Electrical Characteristics (1) for 100 cycle products (D3, D5, U3, U5)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3)		100			cycle
–	Word Program Time (V_{CC1}=5.0V)			25	200	µs
–	Lock Bit Program Time			25	200	µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block		0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
–	Erase All Unlocked Blocks Time (2)				4×n	s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		10			year

Table 5.7 Flash Memory Version Electrical Characteristics (6) for 10,000 cycle products (D7, D9, U7, U9) (Block A and Block 1 (7))

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3, 8, 9)		10,000 (4)			cycle
–	Word Program Time (V_{CC1}=5.0V)			25		µs
–	Lock Bit Program Time			25		µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block		0.3		s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		10			year

NOTES:
1. Referenced to V_{CC1}=4.5 to 5.5V, 3.0 to 3.6V at Topr = 0 to 60 °C (D3, D5, U3, U5) unless otherwise specified.
2. n denotes the number of block erases.
3. Program and Erase Endurance refers to the number of times a block erase can be performed.
   If the program and erase endurance is n (n=100, 1,000, or 10,000), each block can be erased n times.
   For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
4. Maximum number of E/W cycles for which operation is guaranteed.
5. Topr = -40 to 85 °C (D3, D7, U3, U7) / -20 to 85 °C (D5, D9, U5, U9).
6. Referenced to V_{CC1} = 4.5 to 5.5V, 3.0 to 3.6V at T_{opr} = -40 to 85 °C (D7, U7) / -20 to 85 °C (D9, U9) unless otherwise specified.
7. Table 5.7 applies for block A or block 1 program and erase endurance > 1,000. Otherwise, use Table 5.6.
8. To reduce the number of program and erase endurance when working with systems requiring numerous rewrites, write to unused word addresses within the block instead of rewrite. Erase block only after all possible addresses are used. For example, an 8-word program can be written 256 times maximum before erase becomes necessary.
   Maintaining an equal number of erasure between block A and block 1 will also improve efficiency. It is important to track the total number of times erasure is used.
9. Should erase error occur during block erase, attempt to execute clear status register command, then block erase command at least three times until erase error disappears.
10. Set the PM17 bit in the PM1 register to “1” (wait state) when executing more than 100 times rewrites (D7, D9, U7 and U9).
11. Customers desiring E/W failure rate information should contact their Renesas technical support representative.

Table 5.8 Flash Memory Version Program / Erase Voltage and Read Operation Voltage Characteristics (at T_{opr} = 0 to 60 °C(D3, D5, U3, U5), T_{opr} = -40 to 85 °C(D7, U7) / T_{opr} = -20 to 85 °C(D9, U9))

Flash Program, Erase Voltage	Flash Read Operation Voltage
V_{CC1} = 3.3 V ± 0.3 V or 5.0 V ± 0.5 V	V_{CC1}=2.7 to 5.5 V

Table 5.9 Low Voltage Detection Circuit Electrical Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det4}	Low Voltage Detection Voltage (1)	V_{CC1}=0.8V to 5.5V	3.3	3.8	4.4	V
V_{det3}	Reset Level Detection Voltage (1, 2)		2.2	2.8	3.6	V
V_{det4}-V_{det3}	Electric potential difference of Low Voltage Detection and Reset Level Detection		0.3			V
V_{det3s}	Low Voltage Reset Retention Voltage				0.8	V
V_{det3r}	Low Voltage Reset Release Voltage (3)		2.2	2.9	4.0	V

NOTES:
1. $V_{det4} > V_{det3}$.
2. Where reset level detection voltage is less than 2.7 V, if the supply power voltage is greater than the reset level detection voltage, the microcomputer operates with f(BCLK) ≤ 10MHz.
3. $V_{det3r} > V_{det3}$ is not guaranteed.
4. The voltage detection circuit is designed to use when VCC1 is set to 5V.

Table 5.10 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for Internal Power Supply Stabilization During Powering-On	V_{CC1}=2.7V to 5.5V			2	ms
$t_{d(R-S)}$	STOP Release Time				150	µs
$t_{d(W-S)}$	Low Power Dissipation Mode Wait Mode Release Time				150	µs
$t_{d(S-R)}$	Brown-out Detection Reset (Hardware Reset 2) Release Wait Time	V_{CC1}=V_{det3r} to 5.5V		6 (1)	20	ms
$t_{d(E-A)}$	Low Voltage Detection Circuit Operation Start Time	V_{CC1}=2.7V to 5.5V			20	µs

NOTES:
1. When V_{CC1} = 5V.

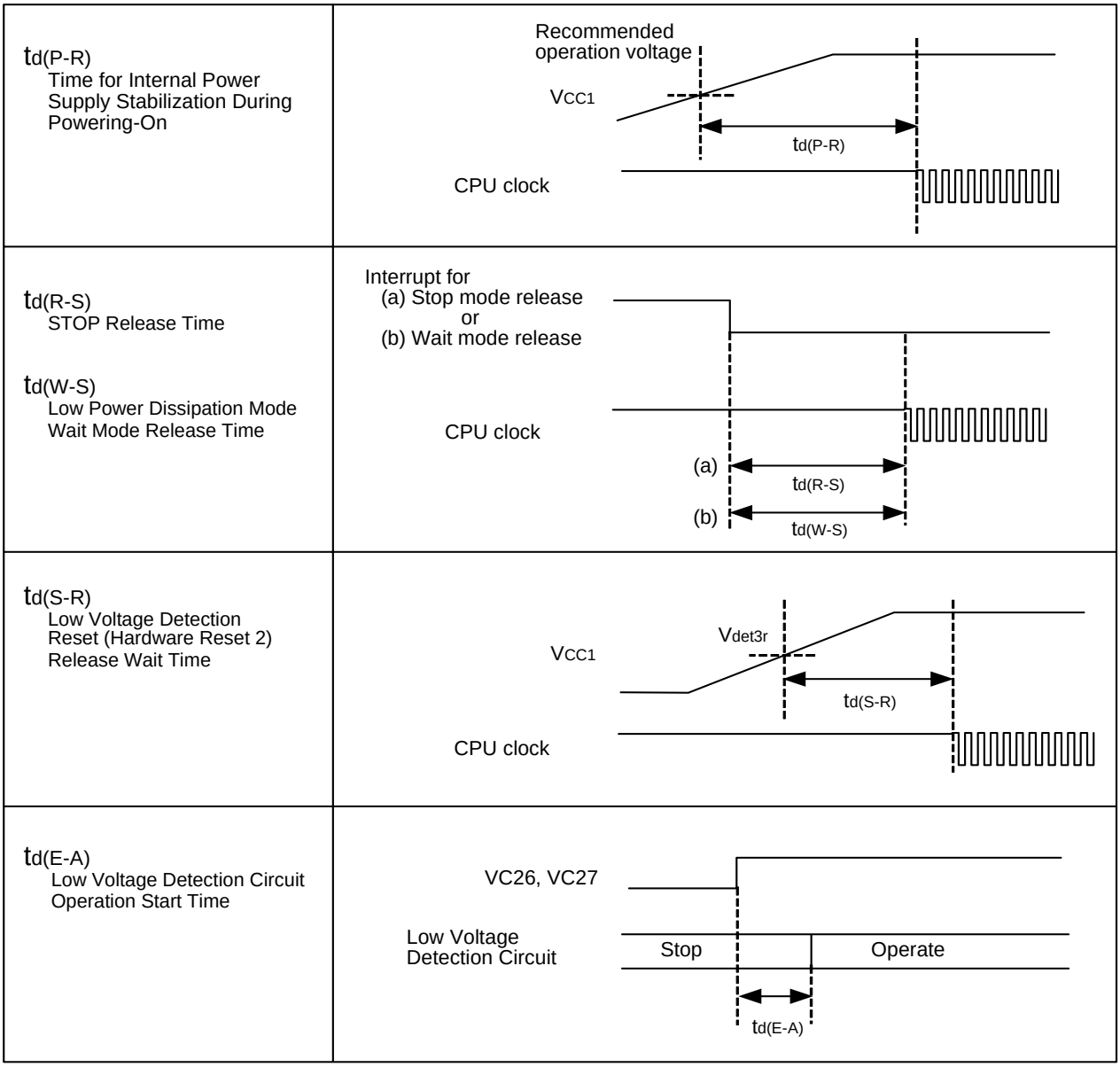


Figure 5.1 Power Supply Circuit Timing Diagram

$V_{CC1}=V_{CC2}=5V$

Switching Characteristics

(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.29 Memory Expansion and Microprocessor Modes (for 2- to 3-wait setting, external area access and multiplex bus selection)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
td(BCLK-AD)	Address Output Delay Time	See **Figure 5.2**		25	ns
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		4		ns
th(RD-AD)	Address Output Hold Time (in relation to RD)		(NOTE 1)		ns
th(WR-AD)	Address Output Hold Time (in relation to WR)		(NOTE 1)		ns
td(BCLK-CS)	Chip Select Output Delay Time			25	ns
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		4		ns
th(RD-CS)	Chip Select Output Hold Time (in relation to RD)		(NOTE 1)		ns
th(WR-CS)	Chip Select Output Hold Time (in relation to WR)		(NOTE 1)		ns
td(BCLK-RD)	RD Signal Output Delay Time			25	ns
th(BCLK-RD)	RD Signal Output Hold Time		0		ns
td(BCLK-WR)	WR Signal Output Delay Time			25	ns
th(BCLK-WR)	WR Signal Output Hold Time		0		ns
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK)		4		ns
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 2)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR)		(NOTE 1)		ns
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns
td(BCLK-ALE)	ALE Signal Output Delay Time (in relation to BCLK)			15	ns
th(BCLK-ALE)	ALE Signal Output Hold Time (in relation to BCLK)		–4		ns
td(AD-ALE)	ALE Signal Output Delay Time (in relation to Address)		(NOTE 3)		ns
th(AD-ALE)	ALE Signal Output Hold Time (in relation to Address)		(NOTE 4)		ns
td(AD-RD)	RD Signal Output Delay From the End of Address		0		ns
td(AD-WR)	WR Signal Output Delay From the End of Address		0		ns
tdz(RD-AD)	Address Output Floating Start Time			8	ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 10[ns]$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5) \times 10^9}{f(BCLK)} - 40[ns]$$

n is “2” for 2-wait setting, “3” for 3-wait setting.

3. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 25[ns]$$

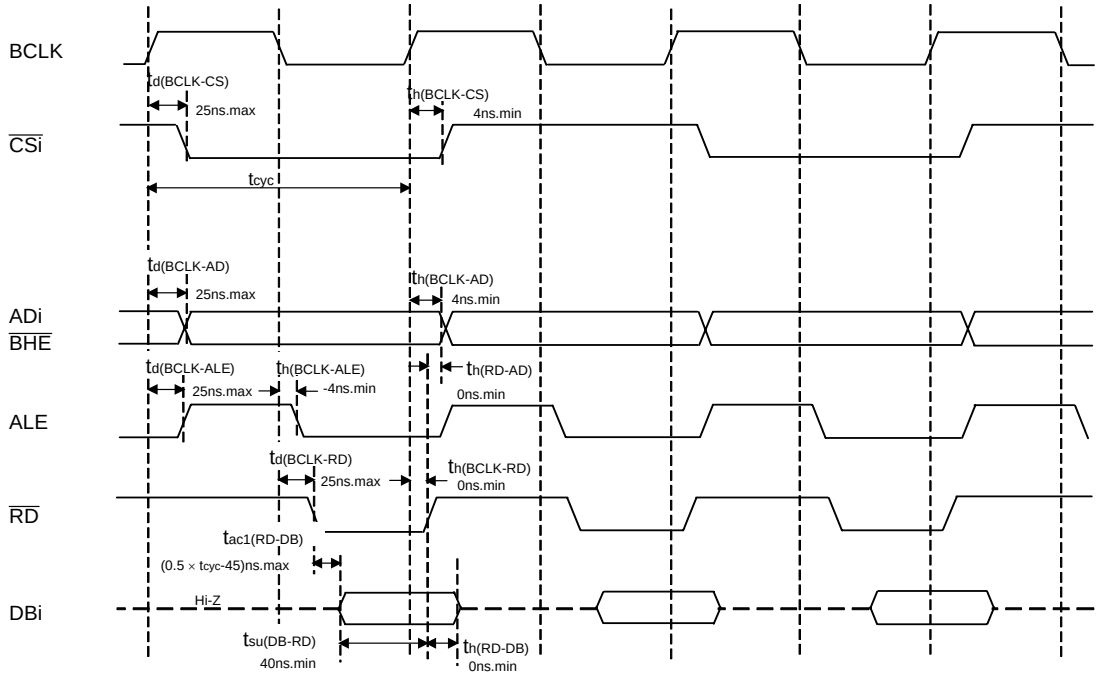
4. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 15[ns]$$

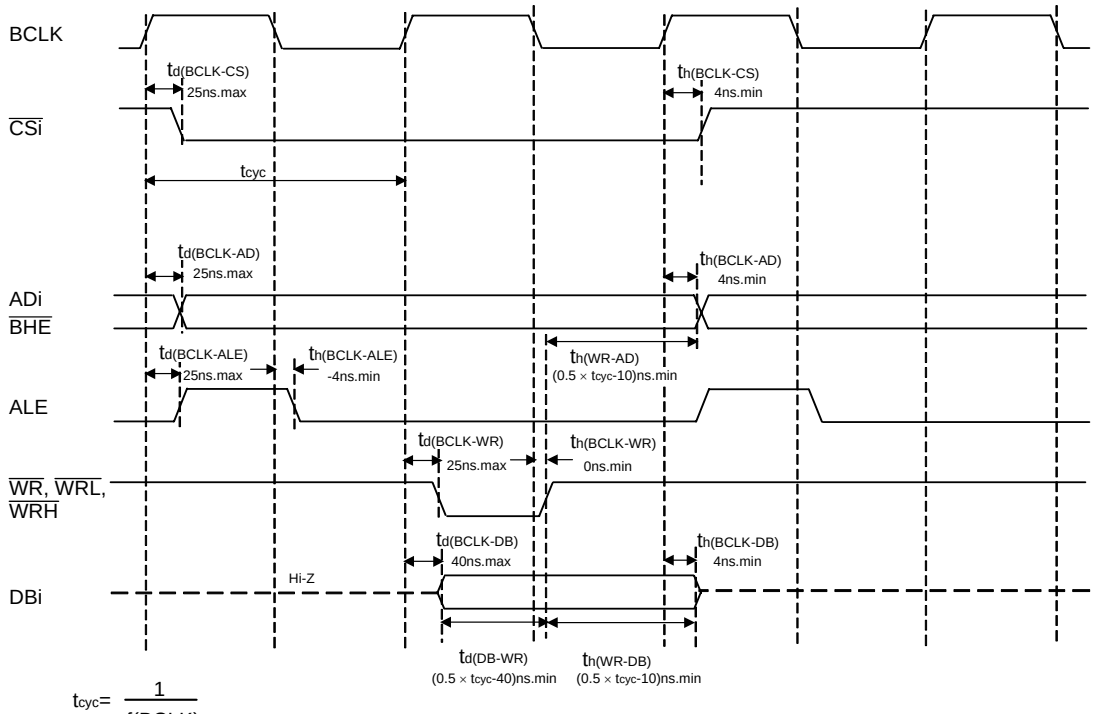
Memory Expansion Mode, Microprocessor Mode
(For setting with no wait**)**

$V_{CC1}=V_{CC2}=5V$

Read timing



Write timing



$$t_{cyc}=\frac{1}{f(BCLK)}$$

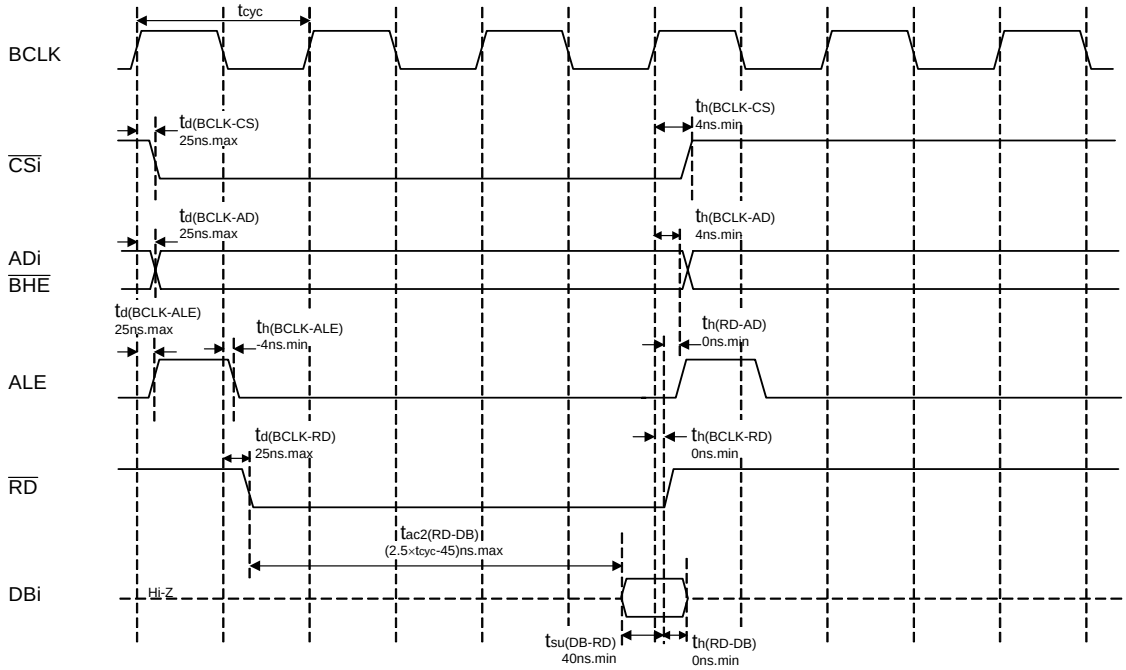
Measuring conditions
· $V_{CC1}=V_{CC2}=5V$
· Input timing voltage : $V_{IL}=0.8V$, $V_{IH}=2.0V$
· Output timing voltage : $V_{OL}=0.4V$, $V_{OH}=2.4V$

Figure 5.6 Timing Diagram (4)

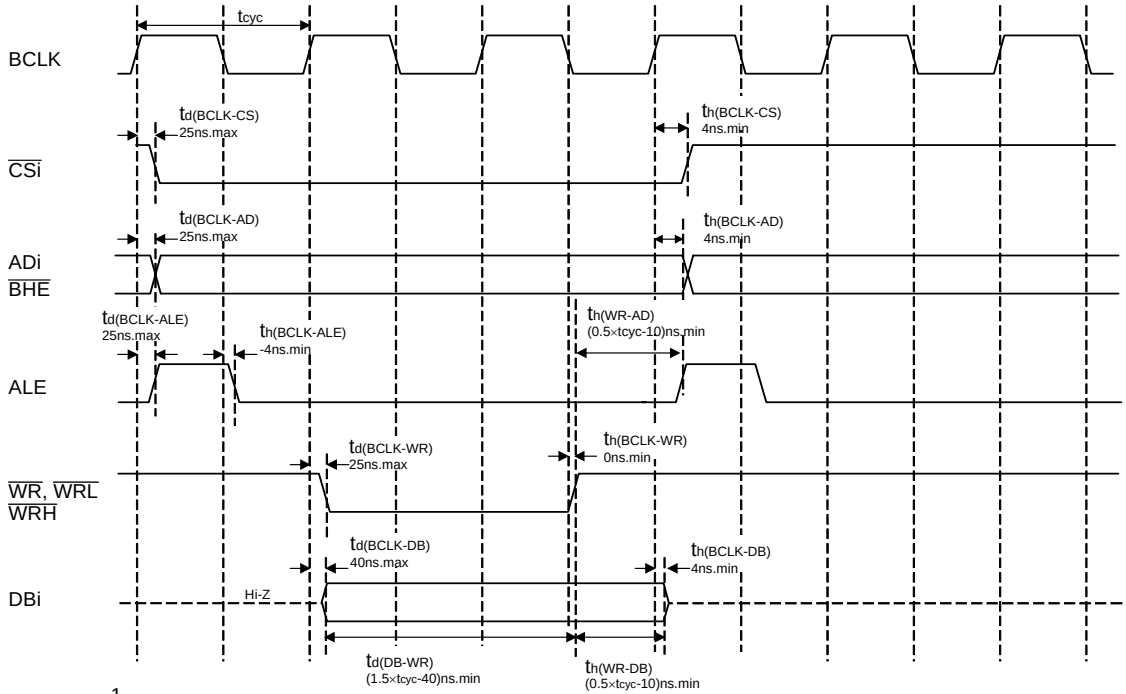
$V_{CC1}=V_{CC2}=5V$

Memory Expansion Mode, Microprocessor Mode
(for 2-wait setting and external area access**)**

Read timing



Write timing



$$T_{cyc}=\frac{1}{f(BCLK)}$$

Measuring conditions
· $V_{CC1}=V_{CC2}=5V$
· Input timing voltage : $V_{IL}=0.8V$, $V_{IH}=2.0V$
· Output timing voltage : $V_{OL}=0.4V$, $V_{OH}=2.4V$

Figure 5.8 Timing Diagram (6)

$V_{CC1}=V_{CC2}=3V$

Timing Requirements
(V_{CC1} = V_{CC2} = 3V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.40 Timer B Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on one edge)	150		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on one edge)	60		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on one edge)	60		ns
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on both edges)	300		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on both edges)	120		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on both edges)	120		ns

Table 5.41 Timer B Input (Pulse Period Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	600		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	300		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	300		ns

Table 5.42 Timer B Input (Pulse Width Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	600		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	300		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	300		ns

Table 5.43 A/D Trigger Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(AD)}$	$\overline{\text{ADTRG}}$ Input Cycle Time	1500		ns
$t_{w(ADL)}$	$\overline{\text{ADTRG}}$ Input LOW Pulse Width	200		ns

Table 5.44 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi Input Cycle Time	300		ns
$t_{w(CKH)}$	CLKi Input HIGH Pulse Width	150		ns
$t_{w(CKL)}$	CLKi Input LOW Pulse Width	150		ns
$t_{d(C-Q)}$	TXDi Output Delay Time		160	ns
$t_{h(C-Q)}$	TXDi Hold Time	0		ns
$t_{su(D-C)}$	RXDi Input Setup Time	100		ns
$t_{h(C-D)}$	RXDi Input Hold Time	90		ns

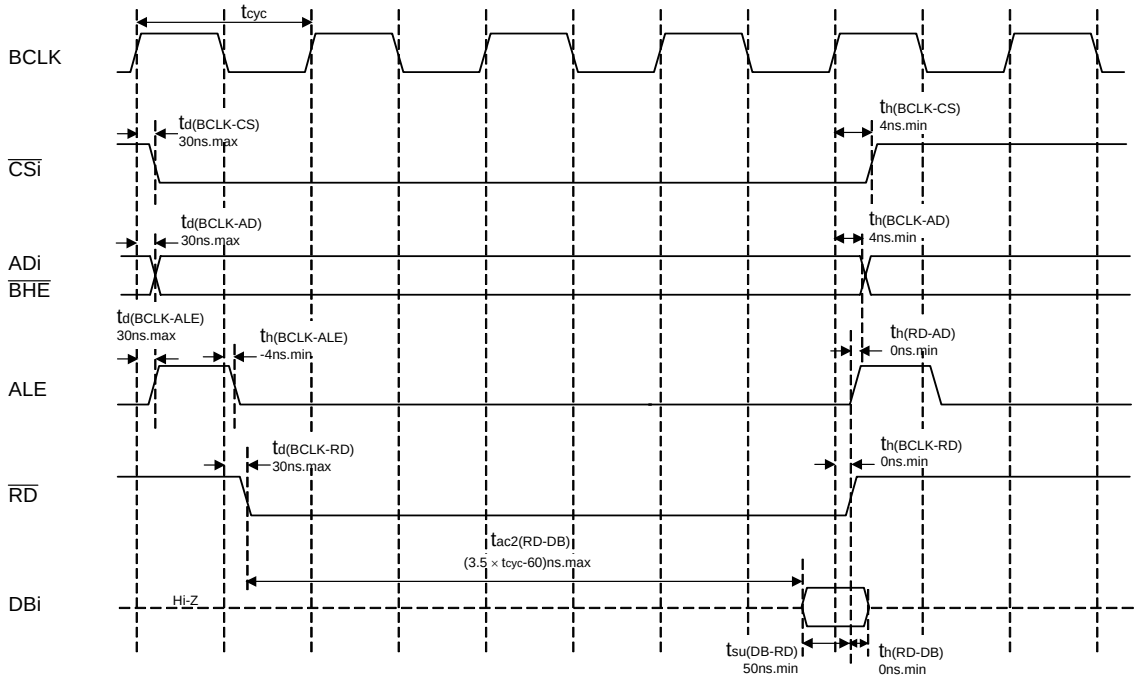
Table 5.45 External Interrupt $\overline{\text{INTi}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{\text{INTi}}$ Input HIGH Pulse Width	380		ns
$t_{w(INL)}$	$\overline{\text{INTi}}$ Input LOW Pulse Width	380		ns

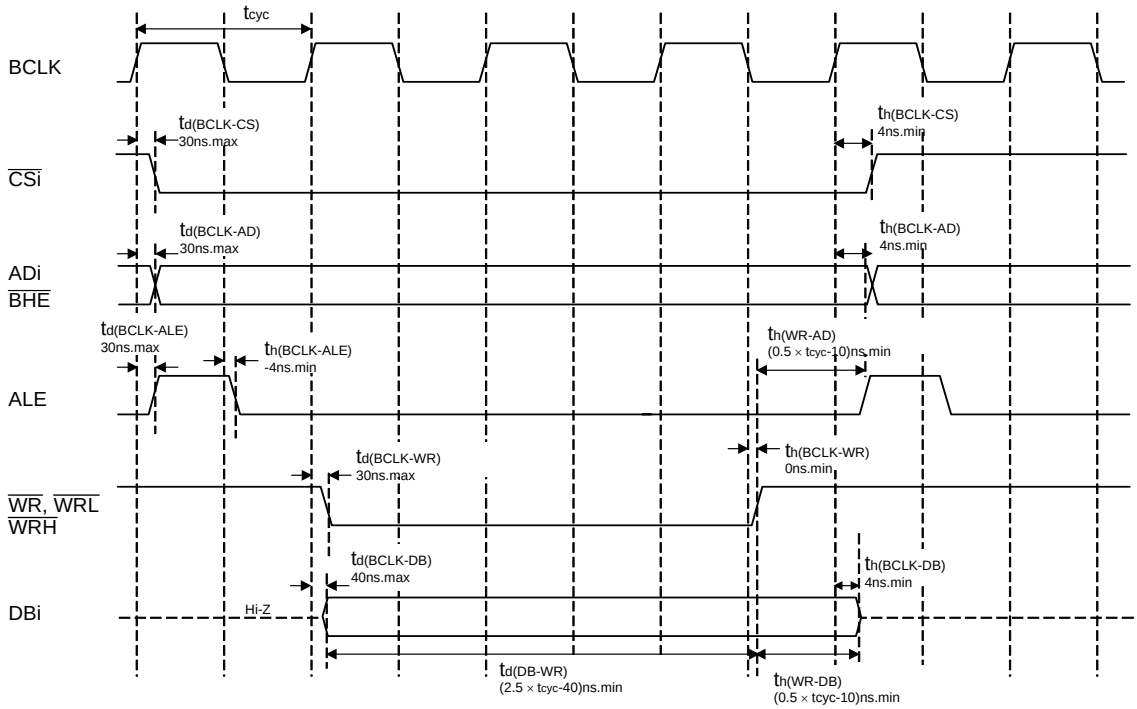
$V_{CC1} = V_{CC2} = 3V$

Memory Expansion Mode, Microprocessor Mode
(for 3-wait setting and external area access**)**

Read timing



Write timing



$$t_{cyc} = \frac{1}{f(BCLK)}$$

Measuring conditions
· V_{CC1}=V_{CC2}=3V
· Input timing voltage : V_{IL}=0.6V, V_{IH}=2.4V
· Output timing voltage : V_{OL}=1.5V, V_{OH}=1.5V

Figure 5.19 Timing Diagram (7)

Table 5.51 A/D Conversion Characteristics (1)

Symbol	Parameter		Measuring Condition		Standard			Unit
					Min.	Typ.	Max.	
–	Resolution		$V_{REF}=V_{CC1}$				10	Bits
INL	Integral Non-Linearity Error	10bit	$V_{REF}=V_{CC1}=5V$	AN0 to AN7 input, AN0_0 to AN0_7 input, AN2_0 to AN2_7 input, ANEX0, ANEX1 input			±3	LSB
				External operation amp connection mode			±7	LSB
		8bit	$V_{REF}=V_{CC1}=5V$				±2	LSB
–	Absolute Accuracy	10bit	$V_{REF}=V_{CC1}=5V$	AN0 to AN7 input, AN0_0 to AN0_7 input, AN2_0 to AN2_7 input, ANEX0, ANEX1 input			±3	LSB
				External operation amp connection mode			±7	LSB
		8bit	$V_{REF}=V_{CC1}=5V$				±2	LSB
–	Tolerance Level Impedance					3		kΩ
DNL	Differential Non-Linearity Error						±1	LSB
–	Offset Error						±3	LSB
–	Gain Error						±3	LSB
R_{LADDER}	Ladder Resistance		$V_{REF}=V_{CC1}$		10		40	kΩ
t_{CONV}	10-bit Conversion Time, Sample & Hold Function Available		$V_{REF}=V_{CC1}=5V$, ϕAD=12MHz		2.75			µs
t_{CONV}	8-bit Conversion Time, Sample & Hold Function Available		$V_{REF}=V_{CC1}=5V$, ϕAD=12MHz		2.33			µs
t_{SAMP}	Sampling Time				0.25			µs
V_{REF}	Reference Voltage				2.0		V_{CC1}	V
V_{IA}	Analog Input Voltage				0		V_{REF}	V

NOTES:
1. Referenced to $V_{CC1}=AV_{CC}=V_{REF}=4.0$ to 5.5V, $V_{SS}=AV_{SS}=0V$ at T_{opr} = –40 to 85°C / –40 to 125°C unless otherwise specified. T version = –40 to 85°C, V version =–40 to 125°C
2. ϕAD frequency must be 12 MHz or less.
3. When sample & hold is disabled, ϕAD frequency must be 250 kHz or more, in addition to the limitation in Note 2. When sample & hold is enabled, ϕAD frequency must be 1MHz or more, in addition to the limitation in Note 2.

Table 5.52 D/A Conversion Characteristics (1)

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
–	Resolution				8	Bits
–	Absolute Accuracy				1.0	%
t_{SU}	Setup Time				3	µs
R_O	Output Resistance		4	10	20	kΩ
I_{VREF}	Reference Power Supply Input Current	(NOTE 2)			1.5	mA

NOTES:
1. Referenced to $V_{CC1}=V_{REF}=4.0$ to 5.5V, $V_{SS}=AV_{SS}=0V$ at T_{opr} = –40 to 85°C / –40 to 125°C unless otherwise specified. T version = –40 to 85°C, V version =–40 to 125°C
2. This applies when using one D/A converter, with the D/A register for the unused D/A converter set to “00h”. The resistor ladder of the A/D converter is not included. Also, when D/A register contents are not “00h”, the I_{VREF} will flow even if Vref id disconnected by the A/D control register.

Table 5.53 Flash Memory Version Electrical Characteristics (1) for 100 cycle products (B, U)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3)		100			cycle
–	Word Program Time (V_{CC1}=5.0V)			25	200	µs
–	Lock Bit Program Time			25	200	µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block	4	0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
–	Erase All Unlocked Blocks Time (2)				4×n	s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		20			year

Table 5.54 Flash Memory Version Electrical Characteristics (6) for 10,000 cycle products (B7, U7) (Block A and Block 1 (7))

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3, 8, 9)		10,000 (4)			cycle
–	Word Program Time (V_{CC}1=5.0V)			25		µs
–	Lock Bit Program Time			25		µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block	4	0.3		s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		20			year

NOTES:
1. Referenced to V_{CC1}=4.5 to 5.5V at T_{opr} = 0 to 60 °C unless otherwise specified.
2. n denotes the number of block erases.
3. Program and Erase Endurance refers to the number of times a block erase can be performed.
   If the program and erase endurance is n (n=100, 1,000, or 10,000), each block can be erased n times.
   For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
4. Maximum number of E/W cycles for which operation is guaranteed.
5. Ta (ambient temperature)=55 °C. As to the data hold time except Ta=55 °C, please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor.
6. Referenced to V_{CC1} = 4.5 to 5.5V at T_{opr} = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version)) unless otherwise specified.
7. Table 5.54 applies for block A or block 1 program and erase endurance > 1,000. Otherwise, use Table 5.53.
8. To reduce the number of program and erase endurance when working with systems requiring numerous rewrites, write to unused word addresses within the block instead of rewrite. Erase block only after all possible addresses are used. For example, an 8-word program can be written 256 times maximum before erase becomes necessary.
   Maintaining an equal number of erasure between block A and block 1 will also improve efficiency. It is important to track the total number of times erasure is used.
9. Should erase error occur during block erase, attempt to execute clear status register command, then block erase command at least three times until erase error disappears.
10. Set the PM17 bit in the PM1 register to “1” (wait state) when executing more than 100 times rewrites (B7 and U7).
11. Customers desiring E/W failure rate information should contact their Renesas technical support representative.

Table 5.55 Flash Memory Version Program/Erase Voltage and Read Operation Voltage Characteristics (at T_{opr} = 0 to 60 °C(B, U), T_{opr} = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version))

Flash Program, Erase Voltage	Flash Read Operation Voltage
V_{CC1} = 5.0 V ± 0.5 V	V_{CC1}=4.0 to 5.5 V

V_{CC1}=V_{CC2}=5V

Timing Requirements
(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –40 to 85°C (T version) / –40 to 125°C (V version) unless otherwise specified)

Table 5.66 Timer B Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on one edge)	100		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on one edge)	40		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on one edge)	40		ns
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on both edges)	200		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on both edges)	80		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on both edges)	80		ns

Table 5.67 Timer B Input (Pulse Period Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	400		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	200		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	200		ns

Table 5.68 Timer B Input (Pulse Width Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	400		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	200		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	200		ns

Table 5.69 A/D Trigger Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(AD)}$	$\overline{\text{ADTRG}}$ Input Cycle Time	1000		ns
$t_{w(ADL)}$	$\overline{\text{ADTRG}}$ input LOW Pulse Width	125		ns

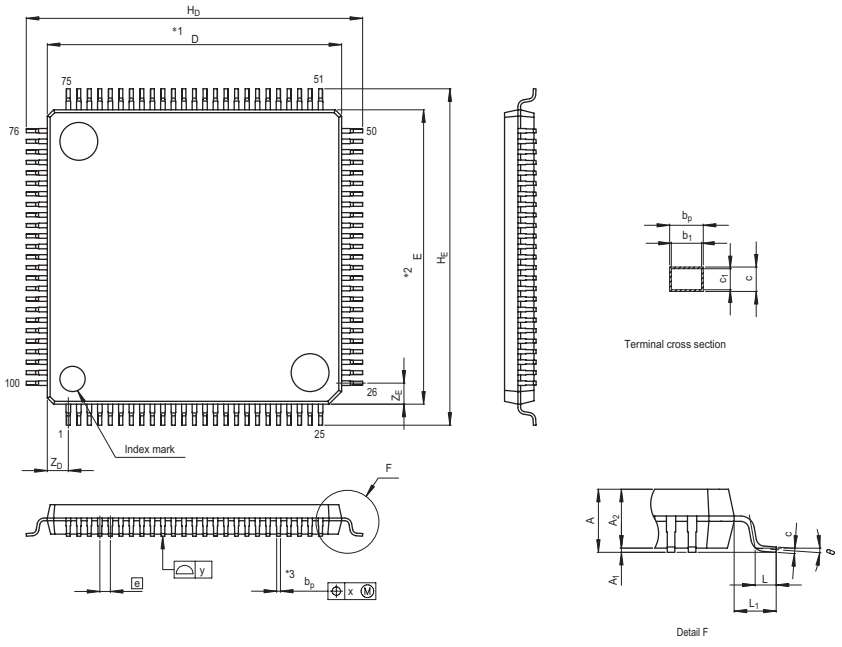
Table 5.70 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi Input Cycle Time	200		ns
$t_{w(CKH)}$	CLKi Input HIGH Pulse Width	100		ns
$t_{w(CKL)}$	CLKi Input LOW Pulse Width	100		ns
$t_{d(C-Q)}$	TXDi Output Delay Time		80	ns
$t_{h(C-Q)}$	TXDi Hold Time	0		ns
$t_{su(D-C)}$	RXDi Input Setup Time	70		ns
$t_{h(C-D)}$	RXDi Input Hold Time	90		ns

Table 5.71 External Interrupt $\overline{\text{INTi}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{\text{INTi}}$ Input HIGH Pulse Width	250		ns
$t_{w(INL)}$	$\overline{\text{INTi}}$ Input LOW Pulse Width	250		ns

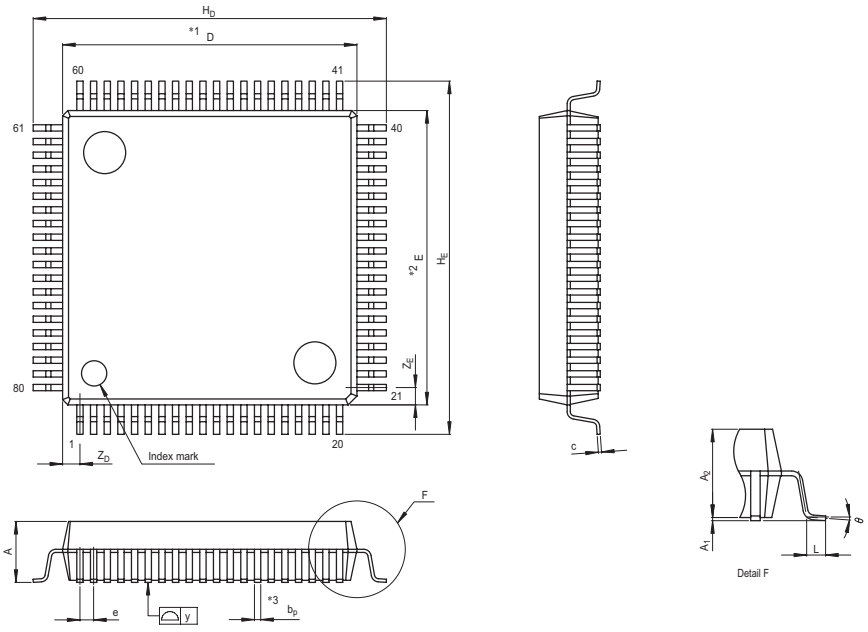
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP100-14x14-0.50	PLQP0100KB-A	100P6Q-A / FP-100U / FP-100UV	0.6g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	13.9	14.0	14.1
E	13.9	14.0	14.1
A_2	—	1.4	—
H_D	15.8	16.0	16.2
H_E	15.8	16.0	16.2
A	—	—	1.7
A_1	0.05	0.1	0.15
b_p	0.15	0.20	0.25
b_1	—	0.18	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
Z_D	—	1.0	—
Z_E	—	1.0	—
L	0.35	0.5	0.65
L_1	—	1.0	—

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-QFP80-14x14-0.65	PRQP0080JA-A	80P6S-A	1.1g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	13.8	14.0	14.2
E	13.8	14.0	14.2
A_2	—	2.8	—
H_D	16.5	16.8	17.1
H_E	16.5	16.8	17.1
A	—	—	3.05
A_1	0	0.1	0.2
b_p	0.25	0.3	0.4
c	0.13	0.15	0.2
θ	0°	—	10°
e	0.5	0.65	0.8
y	—	—	0.10
Z_D	—	0.825	—
Z_E	—	0.825	—
L	0.4	0.6	0.8